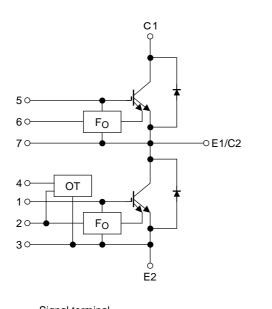
TOSHIBA IGBT Module Silicon N Channel IGBT

MG400Q2YS60A

High Power Switching Applications Motor Control Applications

- Integrates a complete half bridge power circuit and fault-signal output circuit in one package. (short circuit and over temperature)
- The electrodes are isolated from case.
- Low thermal resistance.
- VCE (sat) = 2.4 V (typ.)

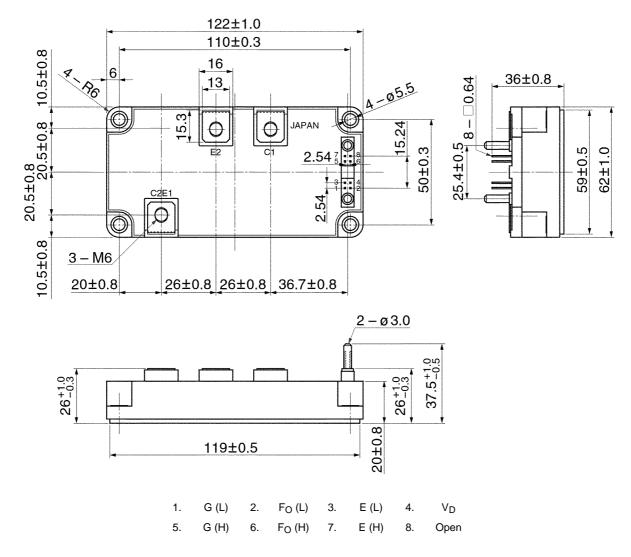
Equivalent Circuit



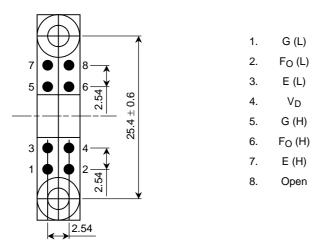
Signa	al terminal						
1.	G (L)	2.	F _O (L)	3.	E (L)	4.	V_{D}
5.	G (H)	6.	F _O (H)	7.	E (H)	8.	Open

Package Dimensions: 2-123C1B

Unit: mm



Signal Terminal Layout





Maximum Ratings (Ta = 25°C)

Stage	Characteristics	Symbol	Rating	Unit	
	Collector-emitter voltage	V _{CES}	1200	V	
	Gate-emitter voltage		V _{GES}	±20	V
	Collector current	DC	Ι _C	400	А
Inverter		1 ms	I _{CP}	800	~
	Forward current	DC	١ _F	400	А
	Forward current	1 ms	I _{FM}	800	A
	Collector power dissipation (Tc =	P _C	3750	W	
	Control voltage (OT)	VD	20	V	
Control	Fault input voltage	VFO	20	V	
	Fault input current	IFO	20	mA	
	Junction temperature	Тј	150	°C	
	Storage temperature range	T _{stg}	-40~125	°C	
Module	Operation temperature range	T _{ope}	-20~100	°C	
	Isolation voltage	V _{isol}	2500 (AC 1 min)	V	
Screw torque				3 (M5)	N∙m

Electrical Characteristics ($T_j = 25^{\circ}C$)

1. Inverter stage

Characteristics		Symbol	Test Condition		Min	Тур.	Max	Unit
Gate leakage current		I _{GES}	$V_{GE} = \pm 20 \text{ V}, \text{ V}_{CE} = 0$		_	_	+3/-4	mA
			$V_{GE} = +10 \text{ V}, \text{ V}_{CE} = 0$			_	100	nA
Collector cut-off current		ICES	$V_{CE} = 1200 V, V_{GE} = 0$		_	_	1.0	mA
Gate-emitter cut-off voltage		V _{GE (off)}	$V_{CE} = 5 \text{ V}, \text{ I}_{C} = 400 \text{ mA}$		6.0	7.0	8.0	V
Collector-emitter saturation voltage		V _{CE (sat)}	V _{GE} = 15 V, I _C = 400 A	Tj = 25°C	_	2.4	2.8	V
				Tj = 125°C		_	3.2	
Input capacitance		Cies	V _{CE} = 10 V, V _{GE} = 0, f = 1 MHz			31000	_	pF
	Turn-on delay time	t _{d (on)}	$V_{CC} = 600 \text{ V}, \text{ I}_{C} = 000 \text{ V}$ $V_{GE} = \pm 15 \text{ V}, \text{ R}_{G} = 00000000000000000000000000000000000$	$CC = 600 \text{ V}, \text{ I}_{C} = 400 \text{ A}$ $GE = \pm 15 \text{ V}, \text{ R}_{G} = 5.1 \Omega$ (Note 1)	0.10	_	1.00	μs
Switching time	Turn-off time	t _{off}				_	2.00	
	Fall time	t _f				_	0.50	
Reverse recovery time		t _{rr}				_	0.50	
Forward voltage		V _F	I _F = 400 A		_	2.4	2.8	V

Note 1: Switching time test circuit & timing chart

2. Control (Tc = 25°C)

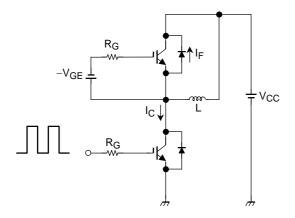
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Fault output current	OC	$V_{GE} = 15 V$	480	_	_	А
Over temperature	OT	—	100	_	125	°C
Fault output delay time	t _{d (Fo)}	$V_{CC}=600~V,~V_{GE}=\pm15~V$	_		8	μs

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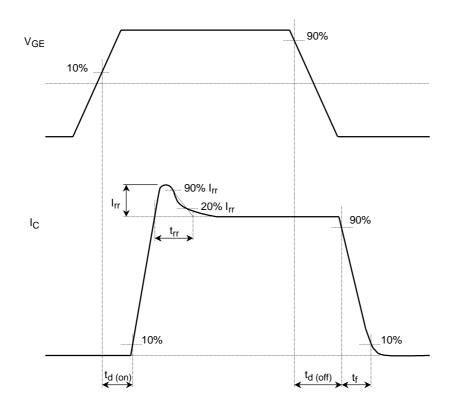
3. Module (Tc = 25° C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Junction to case thermal resistance	Put (1)	Inverter IGBT stage	_	_	0.033	°C/W	
Sunction to case thermal resistance	R _{th (j-c)}	Inverter FRD stage	_	_	0.068	0/11	
Case to fin thermal resistance	R _{th (c-f)}	With silicon compound	_	0.013	_	°C/W	

Switching Time Test Circuit



Timing Chart



Remark

<Short circuit capability condition >

- Short circuit capability is 6 µs after fault output signal. Please keep following condition to use fault output signal.
 - VCC ≤ 750 V
 - 14.8 V \leq VGE \leq 17.0 V
 - $R_G \ge 5.1 \Omega$
 - $T_j \leq 125^{\circ}C$

<Gate voltage >

• To use this product, VGE must be provided higher than 14.8 V In case VGE is less than 14.8 V, fault signal FO may not be output even under error conditions.

<For parallel use>

• For parallel use of this product, please use the same rank for both VCE (sat) and VF among IGBT in parallel without fail.

V _{CE (sat)}	VF	Min	Max
24	E	2.1	2.4
26	F	2.3	2.6
28	G	2.5	2.8

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